In the Claims

CLAIMS

Claims 1-41 (Canceled).

42. (Currently amended) A semiconductor assembly, comprising:

a semiconductor substrate having a pair of electrical nodes supported thereby; the electrical nodes being a first electrical node and a second electrical node, respectively, and at least one of the first and second electrical nodes having a lateral width defined by a pair of isolation regions formed within the semiconductor substrate on opposite sides of the at least one of the first and second electrical nodes;

an insulative mass over the substrate; the mass having a pair of openings extending therethrough to the electrical nodes; the individual openings each having a periphery defined by a bottom and at least one sidewall; the opening extending to the first electrical node being a first opening, and the opening extending to the second electrical node being a second opening;

a dielectric material layer within the openings; the dielectric material layer lining the at least one sidewall and bottom of the first opening, and lining the at least one sidewall but not a predominant portion of the bottom of the second opening;

conductive material plugs within the openings; the conductive material plug within the first opening being a first material plug, and the conductive material plug within the second opening being a second material plug; the first and

second conductive material plugs comprising the same chemically constituencies as one another;

the first electrical node, dielectric material within the first opening, and first conductive material plug together being incorporated into an anti-fuse construction; and

the second electrical node, dielectric material within the second opening, and second conductive material plug together being incorporated into an electrically conductive interconnect construction.

- 43. (Original) The assembly of claim 42 wherein the dielectric material layer comprises silicon nitride.
- 44. (Original) The assembly of claim 42 wherein the both conductive plugs are formed by common and simultaneous processing.
- 45. (Original) The assembly of claim 42 wherein the dielectric material is formed within the pair of openings by common and simultaneous processing.
- 46. (Original) The assembly of claim 42 wherein the dielectric material layer comprises silicon nitride and has a thickness of from about 30Å to about 100Å.

- 47. (Original) The assembly of claim 42 wherein the first electrical node comprises a p-type doped diffusion region within a semiconductive material of the semiconductor substrate.
- 48. (Original) The assembly of claim 42 wherein the first electrical node comprises an n-type doped diffusion region within a semiconductive material of the semiconductor substrate.

Claims 49-52 (Cancelled).

- 53. (Original) The assembly of claim 42 wherein the conductive plugs comprise conductively doped silicon.
- 54. (Original) The assembly of claim 42 wherein the conductive plugs comprise a metal.
- 55. (Original) The assembly of claim 42 wherein the conductive plugs comprise tungsten.
- 56. (Original) The assembly of claim 42 wherein the conductive plugs comprise copper.

- 57. (Original) The assembly of claim 42 wherein the conductive plugs comprise aluminum.
- 58. (Original) The assembly of claim 42 wherein the conductive plugs comprise copper and aluminum.
- 59. (Original) The assembly of claim 42 wherein the conductive plugs comprise a layer of titanium nitride against the dielectric material; and a mass of tungsten over the layer of titanium nitride.
- 60. (New) The assembly of claim 42 wherein the pair of the isolation regions comprise a chemical constituency that is different from a chemical constituency of the insulative mass.
- 61. (New) The assembly of claim 42 wherein the pair of the isolation regions comprise a pair of shallow trench isolation regions.

62. (New) A semiconductor assembly, comprising:

a semiconductor substrate having an upper surface and a pair of electrical nodes supported over and against the upper surface; the electrical nodes being a first electrical node and a second electrical node, respectively;

an insulative mass over the substrate; the mass having a pair of openings extending therethrough to the electrical nodes; the individual openings each having a periphery defined by a bottom and at least one sidewall; the opening extending to the first electrical node being a first opening, and the opening extending to the second electrical node being a second opening;

a dielectric material layer within the openings; the dielectric material layer lining the at least one sidewall and bottom of the first opening, and lining the at least one sidewall but not a predominant portion of the bottom of the second opening;

conductive material plugs within the openings; the conductive material plug within the first opening being a first material plug, and the conductive material plug within the second opening being a second material plug; the first and second conductive material plugs comprising the same chemically constituencies as one another;

the first electrical node, dielectric material within the first opening, and first conductive material plug together being incorporated into an anti-fuse construction; and

the second electrical node, dielectric material within the second opening, and second conductive material plug together being incorporated into an electrically conductive interconnect construction.

- 63. (New) The assembly of claim 62 wherein the first electrical node comprises a metal.
- 64. (New) The assembly of claim 62 wherein the first electrical node comprises copper.
- 65. (New) The assembly of claim 62 wherein the first electrical node comprises aluminum.
- 66. (New) The assembly of claim 62 wherein the first electrical node comprises copper and aluminum.